BLP10H660P; BLP10H660PG

Power LDMOS transistor

AMPLEON

Rev. 1 — 20 December 2016

Product data sheet

1. Product profile

1.1 General description

A 60 W LDMOS power transistor for broadcast and industrial applications in the HF to 1000 MHz band.

Table 1. Application information

Test signal	f	V _{DS}	P_L	Gp	η _D
	(MHz)	(V)	(W)	(dB)	(%)
pulsed RF	720	50	60	18	72

1.2 Features and benefits

- Easy power control
- Integrated dual sided ESD protection enables class C operation and complete switch off of the transistor
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (HF to 1000 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

2. Pinning information

Table 2. Pinning

¬
¬
¬
7
2 1
' <u></u>
aaa-003574
-
1 5
_ 2_
' <u></u>
aaa-003574
-)

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package	ckage				
	Name	Description	Version			
BLP10H660P	HSOP4F	plastic, heatsink small outline package; 4 leads (flat)	SOT1223-2			
BLP10H660PG	HSOP4	plastic, heatsink small outline package; 4 leads	SOT1224-2			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	110	V
V_{GS}	gate-source voltage		-6	+11	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

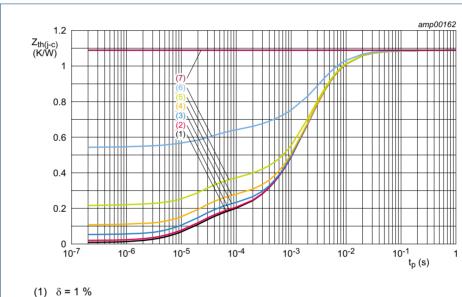
BLP10H660P_BLP10H660PG

Thermal characteristics 5.

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions		Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _j = 125 °C	[1][2]	1.1	K/W
Z _{th(j-c)}	transient thermal impedance from junction to case	T_j = 150 °C; t_p = 100 μs; $δ$ = 20 %	[3]	0.37	K/W

- [1] T_i is the junction temperature.
- $R_{th(j-c)}$ is measured under RF conditions.
- See Figure 1.



- (2) $\delta = 2 \%$
- (3) $\delta = 5 \%$
- (4) $\delta = 10 \%$
- (5) $\delta = 20 \%$
- (6) $\delta = 50 \%$
- (7) $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

Characteristics 6.

DC characteristics Table 6.

 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_{D} = 250 μ A	110	-	-	V
V _{GS(th)}	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 25 mA	1.25	1.9	2.25	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_{D} = 10 \text{ mA}$	-	1.7	-	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	1.4	μΑ

BLP10H660P_BLP10H660PG

Table 6. DC characteristics ...continued

 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	3.9	-	Α
I _{GSS}	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	140	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 0.87 \text{ A}$	-	1.2	-	Ω

Table 7. AC characteristics

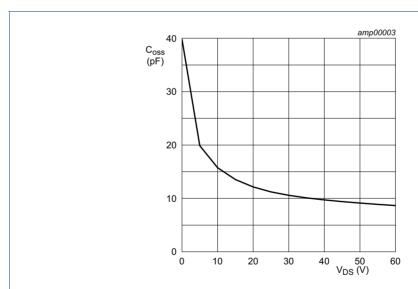
 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	0.15	-	pF
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 50 V; f = 1 MHz	-	28.7	-	pF
Coss	output capacitance	V _{GS} = 0 V; V _{DS} = 50 V; f = 1 MHz	-	9.1	-	pF

Table 8. RF characteristics

Test signal: pulsed RF; t_p = 100 μ s; δ = 20 %; f = 720 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 40 mA; T_{case} = 25 $^{\circ}$ C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _L = 60 W	16.8	18	-	dB
RLin	input return loss	P _L = 60 W	-	-28	-	dB
η_{D}	drain efficiency	P _L = 60 W	70	72	-	%



 $V_{GS} = 0 V$; f = 1 MHz.

Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

7. Test information

7.1 Ruggedness in class-AB operation

The BLP10H660P and BLP10H660PG are capable of withstanding a load mismatch corresponding to VSWR > 40 : 1 through all phases under the following conditions: $V_{DS} = 50 \text{ V}$; $I_{Dq} = 40 \text{ mA}$; $P_L = 60 \text{ W pulsed}$; f = 720 MHz.

7.2 Impedance information

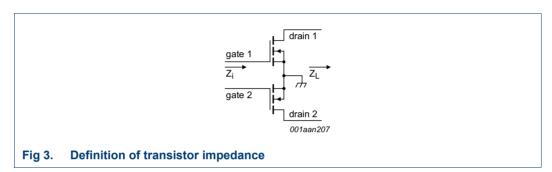
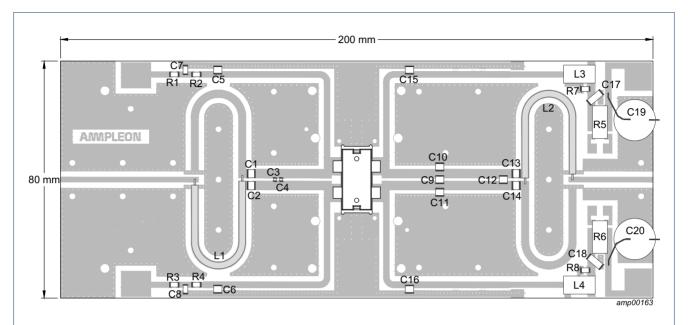


Table 9. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at V_{DS} = 50 V and P_L = 60 W.

f	Z _i	Z _L
(MHz)	(Ω)	(Ω)
720	8.0 – j16.2	16.6 + j22.8

7.3 Test circuit



Printed-Circuit Board (PCB): RF-35; ϵ_r = 3.5 F/m; thickness = 0.765 mm; thickness copper plating = 35 μ m. See Table 10 for a list of components.

Fig 4. Component layout for class-AB production test circuit

Table 10. List of components For test circuit see Figure 4.

Component	Description	Value	Remarks
C1, C2	multilayer ceramic chip capacitor	33 pF	ATC 800B
C3	multilayer ceramic chip capacitor	4.3 pF	ATC 100A
C4	multilayer ceramic chip capacitor	4.7 pF	ATC 100A
C5, C6	multilayer ceramic chip capacitor	150 pF	ATC 100A
C7, C8	electrolytic capacitor	1 μF, 50 V	GRM32RR71H105KA01L
C9	multilayer ceramic chip capacitor	10 pF	ATC 800B
C10, C11	multilayer ceramic chip capacitor	5.6 pF	ATC 800B
C12	multilayer ceramic chip capacitor	5.6 pF	ATC 800B
C13, C14	multilayer ceramic chip capacitor	27 pF	ATC 800B
C15, C16	multilayer ceramic chip capacitor	150 pF	ATC 800B
C17, C18	multilayer ceramic chip capacitor	4.7 μF, 100 V	TDK: C5750X7R2A475KT/A
C19, C20	electrolytic capacitor	1000 μF, 63 V	Vishay
L1	coaxial balun	L = 64.8 mm	EZ_86_TP_M17
L2	coaxial balun	L = 64.8 mm	EZ_86_TP_M17
L3, L4	inductor	90 nH	132-9SMGL
R1, R2, R3, R4	resistor	4.7 Ω	SMD 1206
R5, R6	resistor	50 mΩ, 5 W	FC4L110R010FER
R7, R8	resistor	7.5 Ω	SMD 1206

7.4 Graphical data

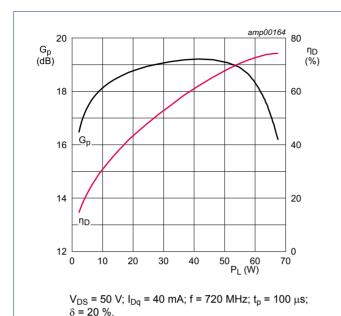
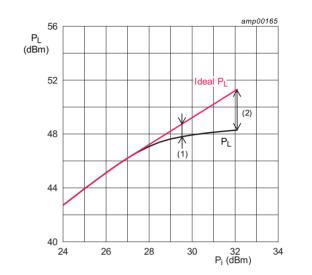


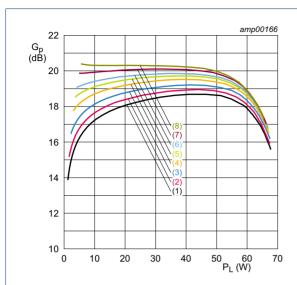
Fig 5. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 50 V; I_{Dq} = 40 mA; f = 720 MHz; t_p = 100 $\mu s;$ δ = 20 %.

- (1) $P_{L(1dB)} = 47.8 \text{ dBm}$ (60 W) at $P_i = 29.5 \text{ dBm}$
- (2) $P_{L(3dB)} = 48.3 \text{ dBm } (67.5 \text{ W}) \text{ at } P_i = 32.1 \text{ dBm}$

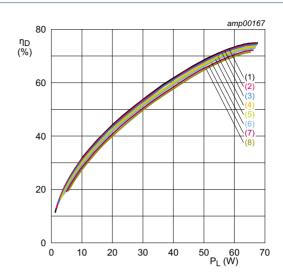
Fig 6. Output power as a function of input power; typical values



 V_{DS} = 50 V; f = 720 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $I_{Dq} = 10 \text{ mA}$
- (2) $I_{Dq} = 20 \text{ mA}$
- (3) $I_{Dq} = 40 \text{ mA}$
- (4) $I_{Dq} = 80 \text{ mA}$
- (5) $I_{Dq} = 120 \text{ mA}$
- (6) $I_{Dq} = 160 \text{ mA}$
- (7) $I_{Dq} = 240 \text{ mA}$
- (8) $I_{Dq} = 320 \text{ mA}$

Fig 7. Power gain as a function of output power; typical values



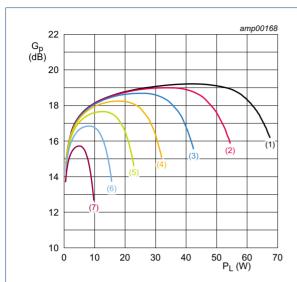
 V_{DS} = 50 V; f = 720 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $I_{Dq} = 10 \text{ mA}$
- (2) $I_{Dq} = 20 \text{ mA}$
- (3) $I_{Dq} = 40 \text{ mA}$
- (4) $I_{Dq} = 80 \text{ mA}$
- (5) $I_{Dq} = 120 \text{ mA}$
- (6) $I_{Dq} = 160 \text{ mA}$
- (7) $I_{Dq} = 240 \text{ mA}$
- (8) $I_{Dq} = 320 \text{ mA}$

Fig 8. Drain efficiency as a function of output power; typical values

BLP10H660P; BLP10H660PG

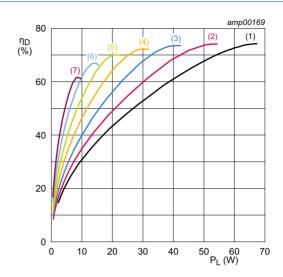
Power LDMOS transistor



 I_{Dq} = 40 mA; f = 720 MHz; t_p = 100 $\mu s;$ δ = 20 %.

- (1) $V_{DS} = 50 \text{ V}$
- (2) $V_{DS} = 45 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 35 \text{ V}$
- (5) $V_{DS} = 30 \text{ V}$
- (6) $V_{DS} = 25 \text{ V}$
- (7) $V_{DS} = 20 \text{ V}$

Fig 9. Power gain as a function of output power; typical values



 I_{Dq} = 40 mA; f = 720 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $V_{DS} = 50 \text{ V}$
- (2) $V_{DS} = 45 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 35 \text{ V}$
- (5) $V_{DS} = 30 \text{ V}$ (6) $V_{DS} = 25 \text{ V}$
- (7) $V_{DS} = 20 \text{ V}$

Fig 10. Drain efficiency as a function of output power; typical values

8. Package outline

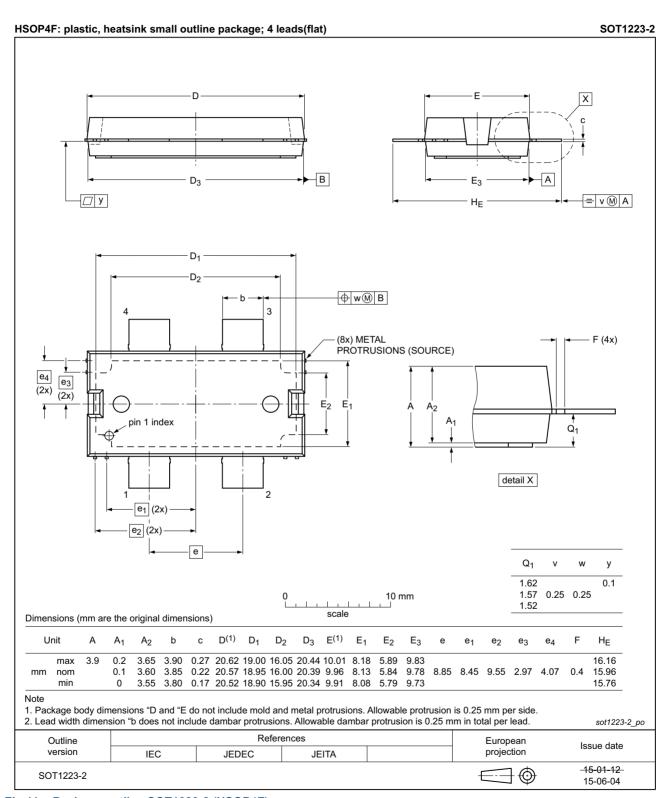


Fig 11. Package outline SOT1223-2 (HSOP4F)

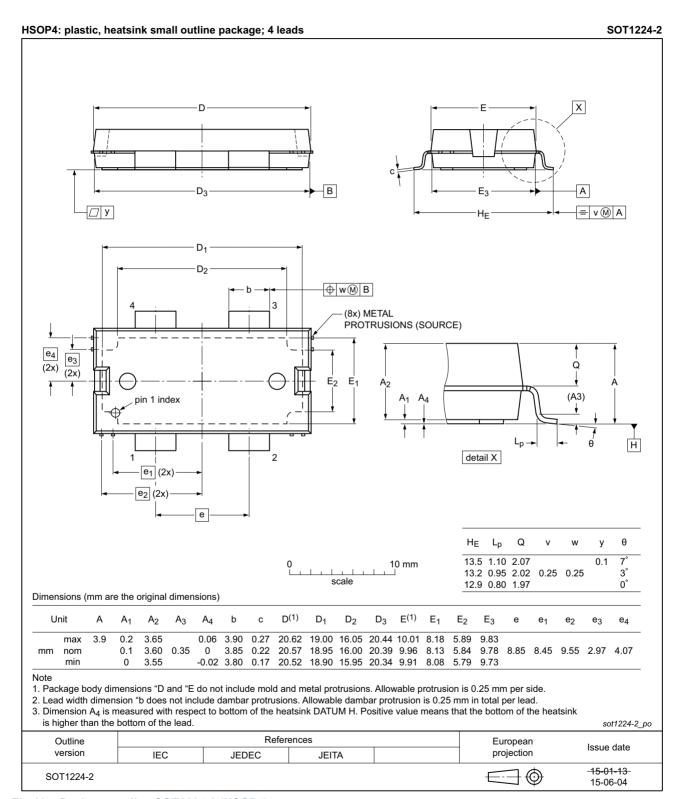


Fig 12. Package outline SOT1224-2 (HSOP4)

Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C1 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1C 2

- [1] CDM classification C1 is granted to any part that passes after exposure to an ESD pulse of 250 V, but fails after exposure to an ESD pulse of 500 V.
- [2] HBM classification 1C is granted to any part that passes after exposure to an ESD pulse of 1000 V, but fails after exposure to an ESD pulse of 2000 V.

10. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP10H660P_BLP10H660PG v.1	20161220	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Ampleon does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Ampleon sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Ampleon and its customer, unless Ampleon and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Ampleon product is deemed to offer functions and qualities beyond those described in the Product data sheet.

12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Ampleon does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Ampleon takes no responsibility for the content in this document if provided by an information source outside of Ampleon.

In no event shall Ampleon be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Ampleon's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Ampleon.

Right to make changes — Ampleon reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Ampleon products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an

Ampleon product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Ampleon and its suppliers accept no liability for inclusion and/or use of Ampleon products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Ampleon makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Ampleon products, and Ampleon accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Ampleon product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Ampleon does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Ampleon products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Ampleon does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Ampleon products are sold subject to the general terms and conditions of commercial sale, as published at http://www.ampleon.com/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Ampleon hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Ampleon products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

BLP10H660P BLP10H660PG

All information provided in this document is subject to legal disclaimers.

© Ampleon Netherlands B.V. 2016. All rights reserved.

BLP10H660P; BLP10H660PG

Power LDMOS transistor

Non-automotive qualified products — Unless this data sheet expressly states that this specific Ampleon product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Ampleon accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Ampleon' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Ampleon' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Ampleon for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Ampleon' standard warranty and Ampleon' product specifications.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

Any reference or use of any 'NXP' trademark in this document or in or on the surface of Ampleon products does not result in any claim, liability or entitlement vis-à-vis the owner of this trademark. Ampleon is no longer part of the NXP group of companies and any reference to or use of the 'NXP' trademarks will be replaced by reference to or use of Ampleon's own trademarks.

13. Contact information

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

AMPLEON

BLP10H660P; BLP10H660PG

Power LDMOS transistor

14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	3
6	Characteristics	3
7	Test information	5
7.1	Ruggedness in class-AB operation	5
7.2	Impedance information	
7.3	Test circuit	
7.4	Graphical data	7
8	Package outline	
9	Handling information	. 12
10	Abbreviations	. 12
11	Revision history	. 12
12	Legal information	. 13
12.1	Data sheet status	. 13
12.2	Definitions	. 13
12.3	Disclaimers	. 13
12.4	Trademarks	. 14
13	Contact information	. 14
1/	Contents	15

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.